

Bh
Gd
a metal layer forming a plurality of top contact electrodes deposited on the p-doped wide energy gap semiconductor layer having patterned regions to confine current conduction in [desired] pixels of said EL device.

B2
3. (once amended) The EL device of claim 1, wherein said CNC layer [are] is selected from the group of semiconductor materials consisting of $Zn_xCd_{1-x}Se$ (core) - $Zn_yMg_{1-y}Se$ (cladding), $Zn_xCd_{1-x}Se$ (core) - $Zn_zBe_{1-z}Se$ (cladding), $Zn_xCd_{1-x}Se$ (core) - $ZnMgSSe$ (cladding), $In_xGa_{1-x}N$ (core) - GaN (cladding), GaN (core) - $AlGaN$ (cladding), and $ZnCdS$ (core) - $ZnMgS$ (cladding), where the subscripts x, y, z represent molar fractions.

B3
5. (once amended) The EL device of claim 1, wherein said CNC layer is sandwiched between lattice-matched wide energy gap semiconductor layers selected from the group of semiconductors consisting of $Zn_aMg_{1-a}Se$, $Zn_aMg_{1-a}S$, $Zn_aMg_{1-a}SbSe_{1-b}$, $Zn_aBe_{1-a}SbSe_{1-b}$, $Al_cGa_{1-c}N$, and $AlInN$, where the subscripts a, b and c represent molar fractions.

B4
6. (once amended) The EL device of claim 1, wherein said p-n junction is reverse-biased electrically to operate said device in the avalanche mode.

7. (once amended) The EL device of claim 1, wherein said p-n junction is forward-biased electrically to operate in injection mode.

B5
8. (once amended) The EL device of claim 1, wherein the layer comprising CNC further comprises multiple sub-layers of differing CNCs sandwiched between epitaxially grown thin film layers of p- and n doped wide energy gap semiconductors.

B6
10. (once amended) The EL device as described in claim 1, wherein said CNC layer has more than one sublayer of differing CNCs stacked to emit different colors and white light .

B7
12. (once amended) The EL device as described in claim 1, wherein more than one said CNC layers are deposited to produce red, green and blue pixel elements for a display panel.

B8
44. (once amended) The EL device as described in claim 1 where the electrodes at the bottom of the device are separated by reverse biased junctions.--

REMARKS

The list of references has been deleted. Missing reference number in Fig.2(a) has been added. Typographical error in the specification has been corrected. Claims 1, 3, 5-8, 10, 12 and 44 have been amended.

The Examiner objected to the listing of references in the application. The list of references has been deleted.